

Dual N-channel 80 V, 30 mΩ logic level MOSFET 17 August 2017

**Product data sheet** 

### 1. General description

Dual Logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC-Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Dual MOSFET
- AEC-Q101 compliant
- Repetitive avalanche rated •
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{GS(th)}$  rating of greater than 0.5 V at 175  $^\circ\text{C}$

### 3. Applications

- 12 V, 24 V and 48 V automotive systems •
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Quick	reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Limiting value	es FET1 and FET2	·				,
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	80	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	17	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	53	W
Static charact	eristics FET1 and FET2	·				
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	21	30	mΩ
Dynamic char	acteristics FET1 and FE	T2				
Q <sub>GD</sub>	gate-drain charge	$\begin{split} I_D &= 5 \text{ A};  \text{V}_{DS} = 64  \text{V};  \text{V}_{GS} = 5  \text{V}; \\ T_j &= 25 ^\circ\text{C};  \overline{\text{Fig. 13}};  \overline{\text{Fig. 14}} \end{split}$	-	6.2	-	nC

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## 5. Pinning information

Table 2. I	Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	S1	source1	8 7 6 5	D1 D1 D2 D2				
2	G1	gate1						
3	S2	source2						
4	G2	gate2						
5	D2	drain2		S1 $G1$ $S2$ $G2$				
6	D2	drain2		mbk725				
7	D1	drain1						
8	D1	drain1	LFPAK56D (SOT1205)					

## 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK9K30-80E	LFPAK56D	plastic, single ended surface mounted package (LFPAK56D); 8 leads; 1.27 mm pitch; 4.7 mm x 5.3 mm x 1.05 mm body	SOT1205				

# 7. Marking

Table 4. Marking codes					
Type number	Marking code				
BUK9K30-80E	93080E				

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
Limiting val	ues FET1 and FET2					
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	80	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	80	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	10	V
		Pulsed; $T_j \le 175 \degree C$	[1] [2]	-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	53	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	17	А
		V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	12	А

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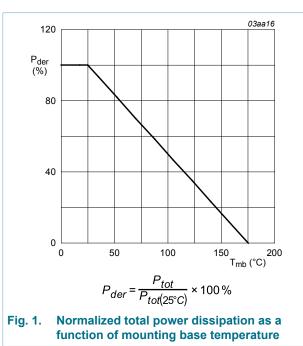
Symbol	Parameter	Conditions		Min	Max	Unit
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	68	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode FET1 and FET2		·			
ls	source current	T <sub>mb</sub> = 25 °C		-	17	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	68	А
Avalanche r	uggedness FET1 and FET2		·			
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:I_star} \begin{array}{l} I_D = 17 \text{ A}; \ V_{sup} \leq \ 80 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 5 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped; \\ \hline Fig. \ 4 \end{array}$	[3] [4]	-	72	mJ

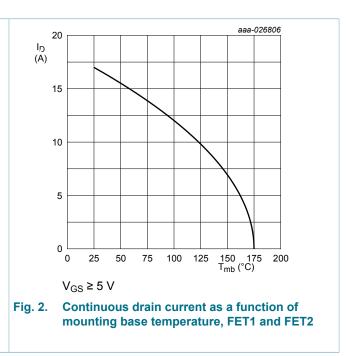
[1] [2] Accumulated Pulse duration up to 50 hours delivers zero defect ppm.

Significantly longer life times are achieved by lowering  $T_j$  and or  $V_{GS}$ .

Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]

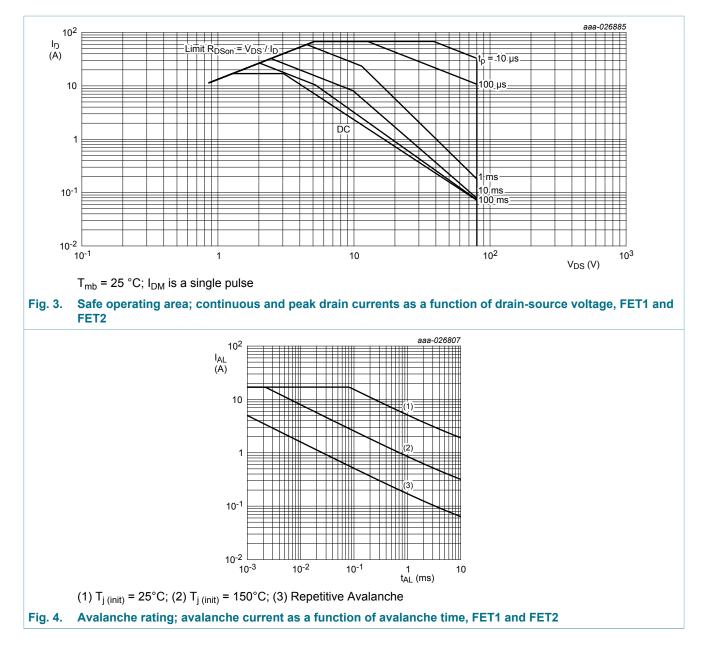
[4] Refer to application note AN10273 for further information.





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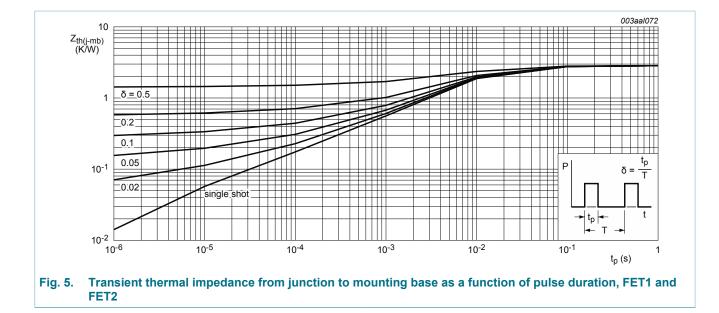


### 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2.84	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

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### **10. Characteristics**

#### **Table 7. Characteristics** Symbol Parameter Conditions Min Тур Max Unit Static characteristics FET1 and FET2 drain-source I<sub>D</sub> = 250 μA; V<sub>GS</sub> = 0 V; T<sub>i</sub> = 25 °C 80 V V<sub>(BR)DSS</sub> \_ \_ breakdown voltage I<sub>D</sub> = 250 μA; V<sub>GS</sub> = 0 V; T<sub>i</sub> = -55 °C 72 V \_ \_ I<sub>D</sub> = 1 mA; V<sub>DS</sub>=V<sub>GS</sub>; T<sub>i</sub> = 25 °C; <u>Fig. 9</u>; V<sub>GS(th)</sub> gate-source threshold 1.4 1.7 2.1 V voltage Fig. 10 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_i = -55 \text{ °C};$ V 2.45 \_ -Fig. 10 I<sub>D</sub> = 1 mA; V<sub>DS</sub>=V<sub>GS</sub>; T<sub>i</sub> = 175 °C; 0.5 V \_ \_ Fig. 10 V<sub>DS</sub> = 80 V; V<sub>GS</sub> = 0 V; T<sub>i</sub> = 25 °C drain leakage current 0.01 1 μA IDSS \_ V<sub>DS</sub> = 80 V; V<sub>GS</sub> = 0 V; T<sub>i</sub> = 175 °C 500 μA \_ V<sub>GS</sub> = 10 V; V<sub>DS</sub> = 0 V; T<sub>i</sub> = 25 °C 2 gate leakage current 100 nA I<sub>GSS</sub> \_ V<sub>GS</sub> = -10 V; V<sub>DS</sub> = 0 V; T<sub>i</sub> = 25 °C 2 100 nA \_ V<sub>GS</sub> = 5 V; I<sub>D</sub> = 5 A; T<sub>i</sub> = 25 °C; <u>Fig. 11</u> drain-source on-state 21 30 mΩ **R**<sub>DSon</sub> \_ resistance V<sub>GS</sub> = 10 V; I<sub>D</sub> = 5 A; T<sub>i</sub> = 25 °C; Fig. 11 20 26 mΩ \_ V<sub>GS</sub> = 5 V; I<sub>D</sub> = 5 A; T<sub>i</sub> = 175 °C; <u>Fig. 12</u> 75 mΩ \_ \_ **Dynamic characteristics FET1 and FET2** total gate charge $I_D = 5 A$ ; $V_{DS} = 64 V$ ; $V_{GS} = 5 V$ ; 17.5 nC Q<sub>G(tot)</sub> --T<sub>i</sub> = 25 °C; <u>Fig. 13</u>; <u>Fig. 14</u> nC Q<sub>GS</sub> gate-source charge 3.9 -Q<sub>GD</sub> 6.2 nC gate-drain charge -\_ V<sub>DS</sub> = 25 V; V<sub>GS</sub> = 0 V; f = 1 MHz; Ciss input capacitance 1727 2297 pF \_ T<sub>i</sub> = 25 °C; <u>Fig. 15</u> Coss output capacitance 126 151 pF \_

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>rss</sub>	reverse transfer capacitance		-	68	93	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 60 V; R <sub>L</sub> = 12 Ω; V <sub>GS</sub> = 5 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>j</sub> = 25 °C	-	10.4	-	ns
t <sub>r</sub>	rise time		-	14.8	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	24.7	-	ns
t <sub>f</sub>	fall time		-	15	-	ns
Source-dra	in diode FET1 and FET2					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 5 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	27.2	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C	-	30.8	-	nC

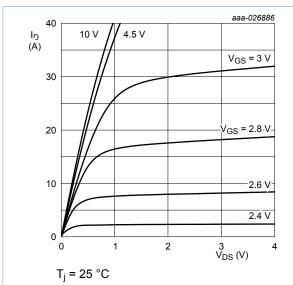


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values, FET1 and FET2

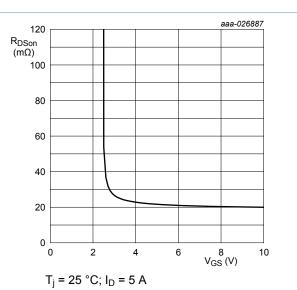
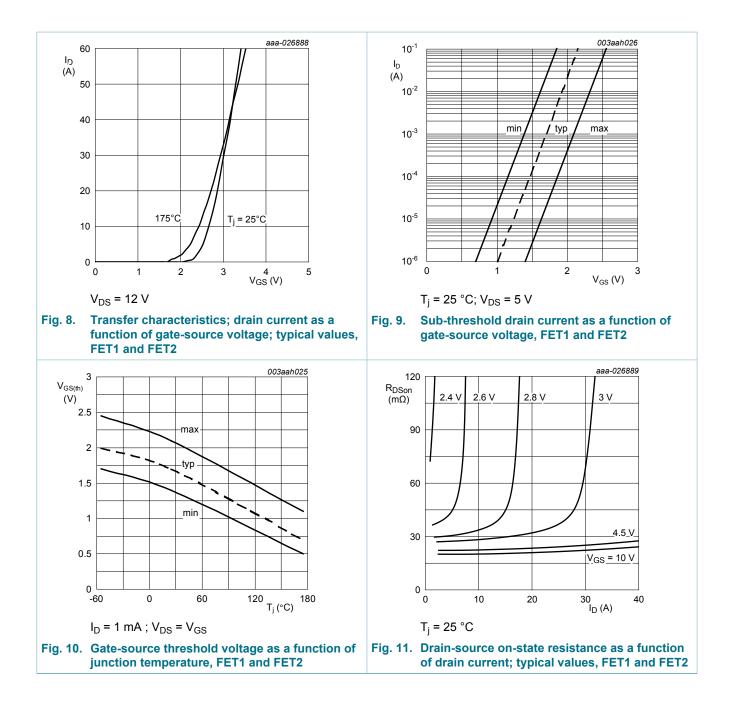


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values, FET1 and FET2

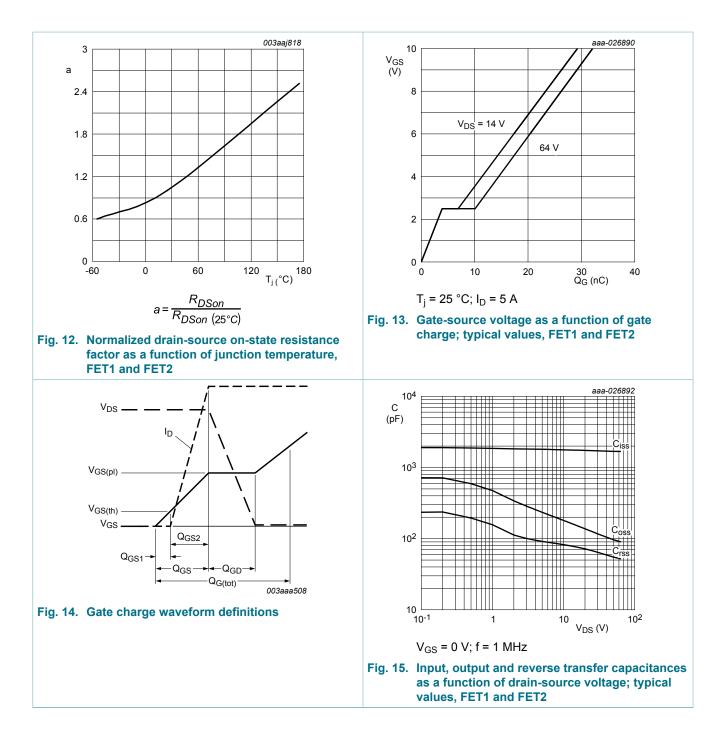
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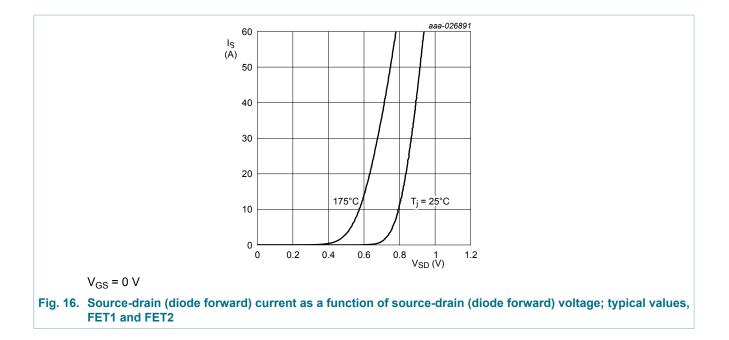
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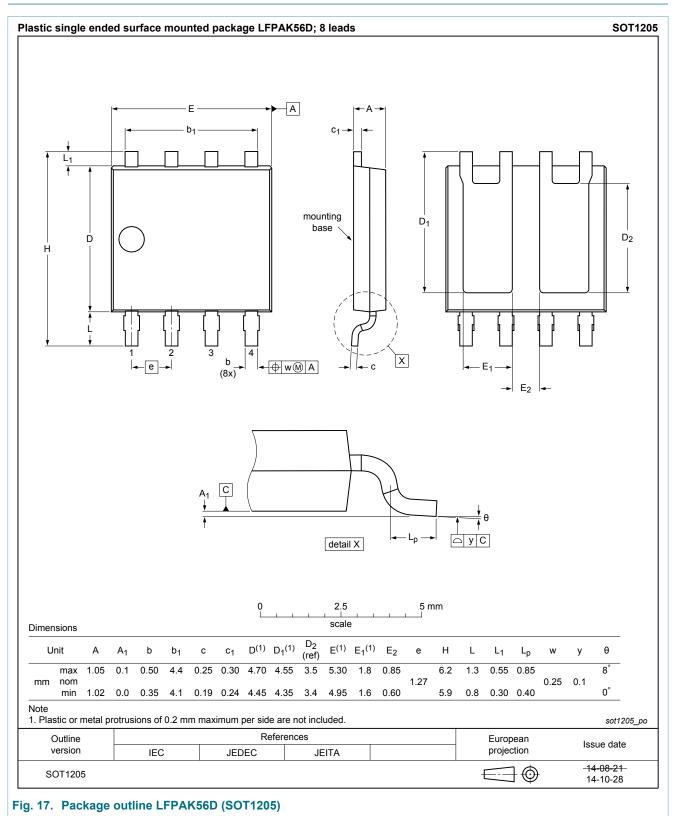
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### **11. Package outline**



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### 12. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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